

## Electronic Acknowledgement Receipt

EFS ID:	9687751
Application Number:	10577175
International Application Number:	
Confirmation Number:	3451
Title of Invention:	Method for Self-Supported Transfer of a Fine Layer by Pulsation after Implantation or Co-Implantation
First Named Inventor/Applicant Name:	Nguyet-Phuong Nguyen
Customer Number:	90678
Filer:	Jasper W. Dockrey/Nkosi Harvey
Filer Authorized By:	Jasper W. Dockrey
Attorney Docket Number:	9905/40 (BIF116533US/)
Receipt Date:	18-MAR-2011
Filing Date:	03-APR-2007
Time Stamp:	16:14:24
Application Type:	U.S. National Stage under 35 USC 371

### Payment information:

Submitted with Payment	no
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### File Listing:

Document Number	Document Description	File Name	File Size(Bytes)/Message Digest	Multi Part/.zip	Pages (if appl.)
1	NPL Documents	Eaglesham_et_al.pdf	272298 560D2e891cd7913254578fd17de7e3d22 897b	no	4

### Warnings:

Information:
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2	NPL Documents	EerNisse_1973.pdf	768866 Ba542ea/69473b33007c/d259c15ff17 1c2	no	8
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**Warnings:****Information:**

3	NPL Documents	EerNisse_et_al_1977.pdf	801341 c1d62586edaf755a0111ba6a2253dc5f9c4 1a10	no	9
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**Warnings:****Information:**

4	NPL Documents	Evans.pdf	869679 da/e361db716168fc79ee119144ef6fe7 #fb6	no	12
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**Warnings:****Information:**

5	NPL Documents	Fukitsuka_et_al.pdf	488514 e2fb2ae1589400bf9647e01293028fa18080fb263 5f5024	no	4
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6	NPL Documents	Garner_et_al.pdf	376649 3ab2d5c6d9647e01293028fa18080fb263 5f5024	no	6
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**Warnings:****Information:**

7	NPL Documents	Gerasimenko_et_al.pdf	423407 0aa7bbdd7d8e94a52f53a5a91e1261c 2e6c2	no	7
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8	NPL Documents	Ghandi.pdf	145184 dcb5200b7d6a70c514698c11a0ff0ff01416e 7917	no	4
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**Warnings:****Information:**

9	NPL Documents	Goesele_et_al_Semiconductor_Wafer_Bonding.pdf	1371808 2cd87a6cb7bd7e6554a053137cb2e652 7bad	no	28
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10	NPL Documents	Greenwald.pdf	364299 294ac2e751b217340f663033312b5f241 d8aa	no	4
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**Warnings:****Information:**

11	NPL Documents	Grovenor_C_Microelectronic_Materials.pdf	183072 d4b89e4d29527fb1e04f92e143630754 2099	no	5
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12	NPL Documents	Guilhalmenç_et_al.pdf	266316 d4b89e4d29527fb1e04f92e143630754 2099	no	4
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**Warnings:****Information:**

13	NPL Documents	Haisma_et_al_Silicon_on_Insulator-Wafer_Bonding.pdf	1279237 3c19415ab698e22e6b1e4f959e74b1b1b6b1 a2c7	no	18
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14	NPL Documents	Hamaguchi_et_al_Device_Layer_Transfer_Technique.pdf	157984 e98f17472e6db1c425d8d156a0f8465ec a2ca	no	3
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15	NPL Documents	Heistand_et_al.pdf	602453 asd98c82e98a22089166f1a2cbf7eb655 d650	no	6
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16	NPL Documents	Hendrix_et_al.pdf	310453 75a7fe5728ef4a21e1e1eebc755ff5c04 4165	no	4
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17	NPL Documents	Huang_et_al.pdf	77104 6e21652acc630061641dfdd6641284e406a2 4e57	no	3
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18	NPL Documents	Hulett_DM_et_al_Ion_Nitriding_and_Ion_Impantation.pdf	228302 894673a4381b7938edc884cb35894da513 34092	no	4
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19	NPL Documents	IBM_Technical_Disclosure_Bulletin_Isolation_By_Inert_Ion_Implantation.pdf	31620 6d41e1872fa5a6a7a39e0bae5dec46 17fc	no	1
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20	NPL Documents	IBM-Tech-Disclosure-SOI-Interposer.PDF	135377 ab769fb46290459ef0ff173be17002114- db4a1	no	5
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21	NPL Documents	Jalaguier_1998.pdf	459037 0f6adfd157bae0daea4ff78x194:5.0kb/fe6ca2- fb309	no	2
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22	NPL Documents	Jalaguier_1999.pdf	204433 d01c511128c312986a3929dd5cf5c26- f5043	no	2
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23	NPL Documents	Jaussaud_C_et_al.pdf	393224 8ecfae0b610d798f0d463380554b5-c0b4- e11	no	3
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24	NPL Documents	Jenei_et_al.pdf	595022 b11fb90bd1b2659e3691aae0e7890:7 d77085	no	7
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25	NPL Documents	Johnson-High_Fluence_Deuteron_Bombardment_of_Silicon.pdf	837642 461086c321720f1d397-0f54632d1095-e- 47f	no	9
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26	NPL Documents	Jones_et_al.pdf	379786 d346990b48959c96d1a89c9a00ff1875- ed705	no	4
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27	NPL Documents	Jones_KS_et_al.pdf	2789593 c0f4ef3bb75fa10e3ca954b3cd4405d9de- b00b	no	35
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28	NPL Documents	Kamada_et_al.pdf	519461 b04feef9fb5e30be0410b7bf66fc160318- d3ef	no	6
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29	NPL Documents	Kim_et_al.pdf	215717 8fa489c9521365a119abdf1bce1135d79ef1 10c8f	no	2
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30	NPL Documents	Klem_et_al.pdf	393669 1bae090e981180070a0fbfd01aa5c3d943f7 c800	no	6
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31	NPL Documents	Komarov_et_al-Crytallographic_Nature_and_Formation.pdf	687131 03abc4940c-e0fb5e11bae92d398c1cb91 581fe	no	9
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32	NPL Documents	Laporte-A-et-al-Charged-Defects-at-the-Interface.pdf	1355175 4674169080e4ba114b7995a895d7bf1bb61 9de5e	no	5
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33	NPL Documents	Li_J_Novel_Semiconductor_Substrate_Formed_By.pdf	51901 9e31e8030c4aa2f60dd07ab3523301d3ec d25518	no	2
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34	NPL Documents	Ligeon_E-Hydrogen_Implantation_in_Silicon_Between_1-5_and_60_KeV.pdf	820674 278fc1c121c5b1cd43208831145982 ccab1	no	9
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35	NPL Documents	Liu_et_al_1999.pdf	724343 06415655899ac56f592eb0c3b26c1010b8 869fc	no	7
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36	NPL Documents	Liu_et_al_2002.pdf	227912 a5904b321be4386e081394ed/a309/f1e972 6def	no	6
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37	NPL Documents	Lu_X-SOI-Material-Technology-Using-Plasma_1.PDF	239638 104711bc6effddaf0e15935a2516ad5e6b 96547	no	2
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38	NPL Documents	Maleville_C_Wafer_Bonding_and_High-Implantation.pdf	266110 4/c05e096b37cfaf7ab03c52423cb3b80f8ba3	no	6
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39	NPL Documents	Maleville-et-al-Physical-Phenomena-Involved_1.PDF	843600 4/af0e5c4241c6aaef9917c024916d90c944	no	18
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40	NPL Documents	Manuaba.pdf	1160732 493-4c311b0a980a6d597c8d0c491941b6755	no	11
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41	NPL Documents	Mastrangelo_C_et_al_Suppression_of_Stiction_in_MEMS.pdf	868944 2ae0fffb1e811e043a9b9cb1973b5a6fe3de7d	no	12
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42	NPL Documents	Matsuda_et_al.pdf	129012 f0795c5000c222f9b5f6ce23b1cd1b972c2e2	no	3
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43	NPL Documents	Matsuo_et_al.pdf	207625 99454fffb5f76d-cb3c95e6b41c878144f0ff	no	3
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44	NPL Documents	Mishima_Y_and_T_Yagishita_Investigation_Of_The_Bubble_Formation.pdf	165000 6db7c0f1210be721abb6b9a4cb3b266f88d2	no	3
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45	NPL Documents	Miyagaw_S_et_al.pdf	774178 c72x333426840c26c5737bb161857f947cc0d	no	9
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46	NPL Documents	Miyagawa_S_et_al-Helium_Reemission_During_Implantation_of_Silicon_Carbide.pdf	375866 c0b902866e030477d3cd2a9e7c5b7d4f408249	no	5
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47	NPL Documents	Monemar_B-Shallow_Impurities_in_Semiconductors.pdf	485747 adff11312dd8ff692/Mfbde17710e995c5 5e94	no	6
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48	NPL Documents	Moreau_Wayne_M_Semiconductor_Lithography_Principles.pdf	497940 b6944d0451ef12e2c742510ac2569e0eb2 adfb	no	17
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49	NPL Documents	Moriceau_H_et_al_A_New_Characterization_Process_Used_To.pdf	303042 0e0f1d48d702bd8fbfc15e2491e6bb9c2 35.000	no	6
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50	NPL Documents	Moriceau_H_et_al_Cleaning_and_Polishing_As_Kep_Steps.pdf	151493 0e3de61952e1e9f0235a05b25f5e247a6 eecc96	no	2
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51	NPL Documents	Moriceau_H_et_al_The_Smart_Cut_Process_As_A_Way_To.pdf	116346 1aa0fb36186c0833845194ec202917cfba ee871	no	2
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52	NPL Documents	Moriceau_Vol99-1_Meeting_Abstract.pdf	156085 a8463749da5f62986b40220499bf795e4 7a8b	no	2
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53	NPL Documents	Motohiro-et-al_1.pdf	787663 61640204e0857e6b800a01afcb1652262 b14	no	15
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54	NPL Documents	Munteanu-et-al-Detailed-Characteristics-of-Unibond-Material.pdf	186594 060f91ace59b031c0f2ac26513415234b a52a	no	4
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55	NPL Documents	Myers_DR-The_Effects_of_Ion-Implantation_Damage_on_The_First_Order_Raman_Spectra.pdf	676976 5a822e6a3c3ab9811529803a03ed7b/e34 d2f7c	no	7
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56	NPL Documents	Neethling_CE_et_al-Identification_of_Hydrogen_Plantelets_in_Proton_Bombardment_GaAs.pdf	436026 b8c65eff4886cadf19861482af02837780197	no	5
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57	NPL Documents	Nichols_C_et_al_Properties_of_Hydrogen_in_Crystalline_Silicon.pdf	740397 10ef72d99e4ec2b7d53fbfc180d7ed3d18c36d78	no	4
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58	NPL Documents	Nicoletti_S_et_al_Bi-Epitaxial_YBCO_Grain_Boundary_Josephson_Junctions.pdf	869860 0faef389171ce12d4990129bd7925fe672d0226	no	13
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59	NPL Documents	Ono_et_al_Orientation_Dependence_of_Flaking_of_Ion_Irradiated.pdf	349210 99628bfef6a332091948bc73b43b172c79 46db	no	6
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60	NPL Documents	Paszti_et_al.pdf	811448 098056254d5ebfb7636212c91a605ef0f3e081d	no	8
<b>Warnings:</b>					
<b>Information:</b>					
<b>Total Files Size (in bytes):</b> 31408215					
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